

17.3-21.5GHz 4W GaN Power Amplifier

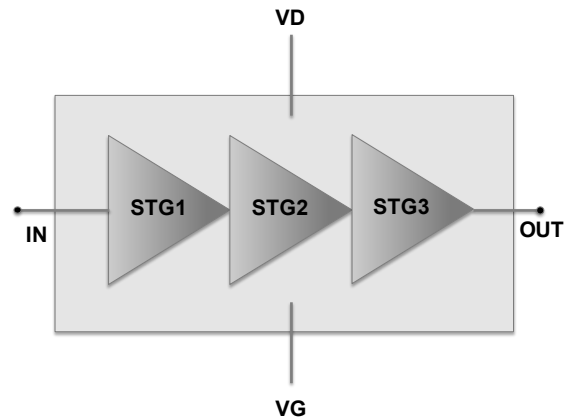
GaN Monolithic Microwave IC

Description

The CHA6262-99F is a three-stage GaN High Power Amplifier operating in the frequency band 17.3-21.5GHz. This HPA typically provides 4W output power associated to 36% of Power Added Efficiency. The circuit exhibits a typical small signal gain of 30dB. The overall power supply is 18V/182mA.

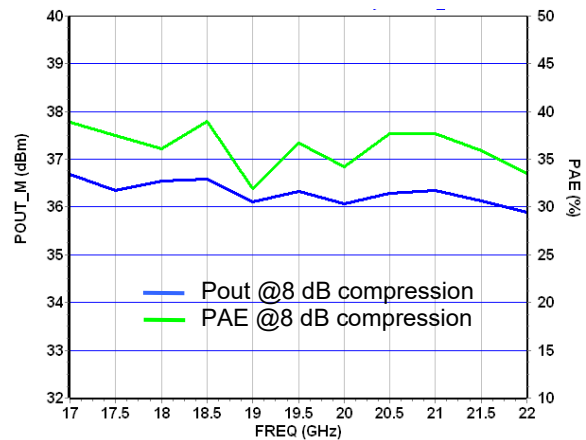
This HPA is dedicated to Space applications and well suited for a wide range of microwave applications and systems.

The product is developed on a robust 0.15µm gate length GaN on SiC HEMT process and is available as a bare die.



Main Features

- 17.3-21.5GHz frequency range
- Linear gain is 30 dB
- $P_{out}=36\text{dBm}$ for $P_{in}=14\text{dBm}$
- $\text{NPR} > 17\text{dB}$ for $P_{out} = 2\text{Watts}$
- $\text{PAE}=36\%$ at P_{sat}
- DC bias: $V_d=18\text{Volts}$ @ $I_{dq}=182\text{mA}$
- Chip size : 3.55mmx2.24mm



Main Electrical Characteristics

$T_{case} = +25^{\circ}\text{C}$

T_{case} : Chip backside temperature

| Symbol | Parameter | Min | Typ | Max | Unit |
|-----------|------------------------|------|-----|------|------|
| Freq | Frequency range | 17.3 | | 21.5 | GHz |
| Gain | Linear Gain | | 30 | | dB |
| PAE | Power Added Efficiency | | 36 | | % |
| P_{sat} | Saturated Output Power | | 36 | | dBm |

These values are representative of the measurements done in an evaluation board.

Specifications (CW mode) $T_{case} = +25^{\circ}\text{C}$, $V_d = +18\text{V}$, $I_{dq} = 182\text{mA}$

| Symbol | Parameter | Min | Typ | Max | Unit |
|-----------|--------------------------------------------|------|-----|------|------|
| Freq | Frequency range | 17.3 | | 21.5 | GHz |
| Gain | Linear Gain | | 30 | | dB |
| S_{11} | Input return loss | | 16 | | dB |
| S_{22} | Output return loss | | 10 | | dB |
| P_{sat} | Saturated output Power | | 36 | | dBm |
| NPR | Noise Power Ratio @ $P_{out}=2\text{Watt}$ | | 17 | | dB |
| PAE | Power Added Efficiency | | 36 | | % |
| I_{dq} | Quiescent Current | | 182 | | mA |
| V_d | Drain Voltage | | 18 | | V |

“Power ON” sequence

1. Ground the device
2. Set the gate voltage to -5V
3. Apply the drain voltage V_d (Typically 18V)
4. Increase V_g up to quiescent bias drain current I_{dq}
5. Apply RF signal

“Power OFF” sequence

1. Turn off RF signal
2. Decrease the gate voltage to -5V
3. Decrease the drain voltage to 0V
4. Turn off V_d supply
5. Turn off V_g supply

Absolute Maximum Ratings ⁽¹⁾T_{case} = +25°C

| Symbol | Parameter | Values | Unit |
|-----------------|---------------------------------------------------|----------|------|
| V _d | Drain bias voltage | 27 | V |
| I _d | Drain bias current (with RF signal at saturation) | 1.1 | mA |
| V _g | Gate bias voltage | -7 to -2 | V |
| P _{in} | Maximum input power | 20 | dBm |

⁽¹⁾ Operation of this device above anyone of these parameters may cause permanent damage.

Recommended Operating Range ^{(2), (3)}

| Symbol | Parameter | Values | Unit |
|-----------------|---------------------------------------------|----------------|------|
| V _d | Drain bias voltage | 18 to 25 | V |
| I _d | Drain bias current (without RF) | 182 to 260 | mA |
| V _g | Gate bias voltage | ~ -2.5 to ~ -3 | V |
| P _{in} | Maximum input power | 18 | dBm |
| T _j | Maximum Junction temperature ⁽⁴⁾ | 200 | °C |

⁽²⁾ Electrical performances are defined for specified test conditions

⁽³⁾ Electrical performances are not guaranteed over all recommended operating conditions

⁽⁴⁾ Value is provided for T_{case}=115°C

Temperature Range

| | | | |
|-------------------|-----------------------------|-------------|----|
| T _{case} | Operating temperature range | -40 to +95 | °C |
| T _{stg} | Storage temperature range | -55 to +150 | °C |

Typical Bias ConditionsT_{case} = +25°C

| Symbol | Pad N° | Parameter | Values | Unit |
|----------------|---------------|---------------|--------|------|
| V _g | 2, 4, 7, 13 | Gate Voltage | ~ -2.7 | V |
| V _d | 9, 11, 16, 17 | Drain Voltage | 18 | V |

Device thermal performances

The thermal performances of the device are based on UMS rules to evaluate the junction temperature (T_j). This temperature is defined as the peak temperature in the channel area. This same procedure is the basis for junction temperature evaluation of the samples used to derive the Median lifetime and activation energy for the particular technology on which the CHA6262-99F is fabricated (GaN Power PHEMT 0.15 μ m).

The temperature is monitored at the backside of the chip (T_{case}).

The system maximum temperature must be adjusted in order to guarantee that junction temperature T_j remains below the maximum value specified in the Recommended Operating Range table. So, the system PCB must be designed to comply with this requirement.

The thermal resistance (R_{TH}) is given in the tables below for the full circuit in CW mode.

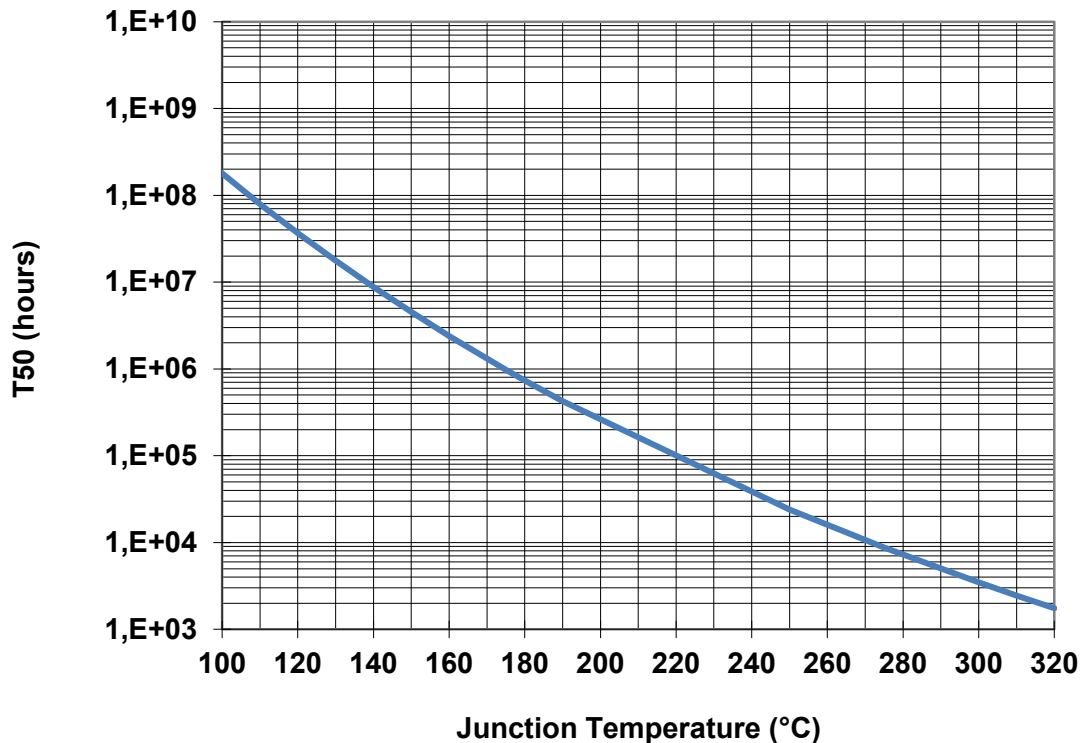
| Parameter | Biasing conditions | T_j (°C) | R_{TH} (°C/W) | T50 (hours) |
|------------------------------------------------------------|---------------------------------|---------------|--------------------|----------------|
| $R_{TH}^{(1)}$ Thermal Resistance (Junction to Case) | Psat=36.3dBm Pdiss= 9.71W CW | 195 | 8.24 | 3.25E+05 |

¹ Assuming $T_{case} = 115^\circ\text{C}$

| Parameter | Biasing conditions | T_j (°C) | R_{TH} (°C/W) | T50 (hours) |
|------------------------------------------------------------|---------------------------------|---------------|--------------------|----------------|
| $R_{TH}^{(2)}$ Thermal Resistance (Junction to Case) | Psat=36.6dBm Pdiss= 8.67W CW | 153 | 7.84 | 3.73E+06 |

² Assuming $T_{case} = 85^\circ\text{C}$

Median Life Time versus Junction Temperature



Typical Package Sij parameters

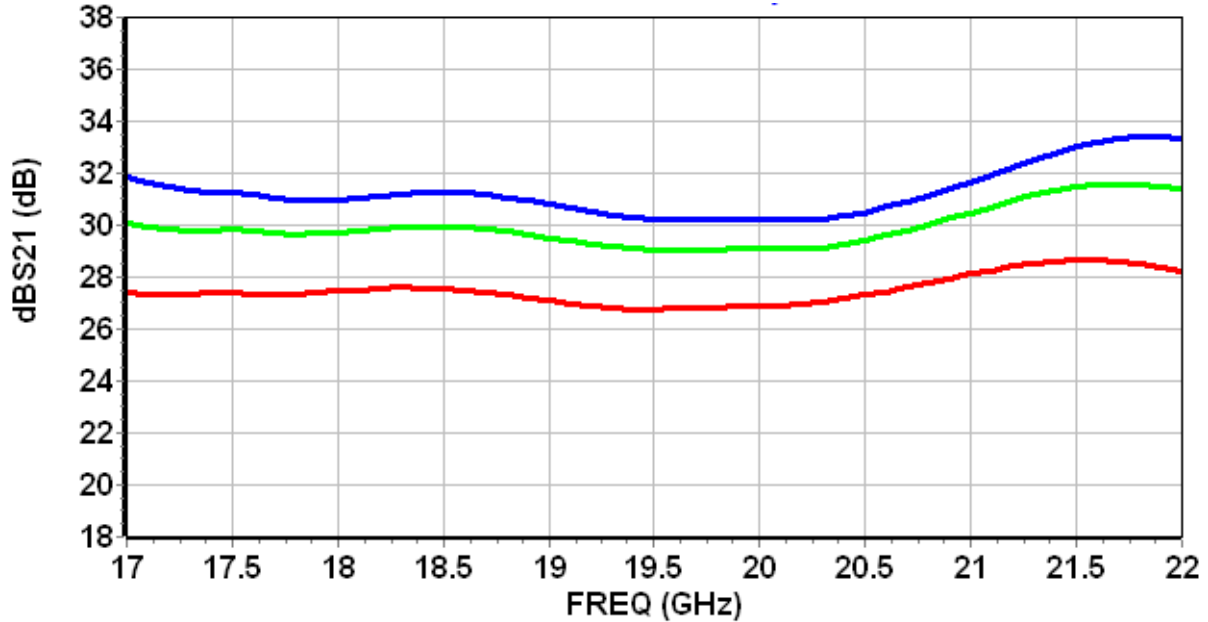
$T_{case} = +25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$

| Freq (GHz) | dBS11 | PhS11 | dBS12 | PhS12 | dBS21 | PhS21 | dBS22 | PhS22 |
|------------|--------|---------|--------|---------|--------|---------|--------|---------|
| 1 | -0.94 | -4.83 | -77.44 | 37.93 | -74.65 | 117.98 | -0.71 | 117.23 |
| 2 | -0.93 | -30.17 | -69.53 | -161.6 | -32.95 | 58.18 | -0.7 | 56.56 |
| 3 | -0.95 | -86.24 | -67.59 | 154.68 | -49.63 | -0.7 | -0.63 | -3.37 |
| 4 | -1 | -147.86 | -67.19 | -126.51 | -48.18 | -60.91 | -0.61 | -63.64 |
| 5 | -1.25 | 146.74 | -67.01 | 134.85 | -33.93 | -124.12 | -0.66 | -125.79 |
| 6 | -1.63 | 118.92 | -72.04 | -33.53 | -23.12 | 167.67 | -0.83 | 169.36 |
| 7 | -1.98 | 134.3 | -81.6 | -162.84 | -29.88 | 92.07 | -1.08 | 101.27 |
| 8 | -2.38 | -0.05 | -82.1 | 108.61 | -35.87 | 5.37 | -1.56 | 28.14 |
| 9 | -3.01 | -162.64 | -63.52 | 131.37 | -47.14 | -101.05 | -3.88 | -50.77 |
| 10 | -3.28 | 107.93 | -59.29 | 106.79 | -30.56 | 129.97 | -5.76 | -86.55 |
| 11 | -2.97 | 39.6 | -57.9 | -12.12 | -25.28 | 11.51 | -2.71 | -161.42 |
| 12 | -3.1 | -37.88 | -59.32 | -103.05 | -29.82 | -79.82 | -1.85 | 110.96 |
| 13 | -3.65 | -31.99 | -65.73 | -48.82 | -33.43 | -156.93 | -1.62 | 11.62 |
| 14 | -4.59 | -87.94 | -57.97 | -38.51 | -9.89 | 130.36 | -2.38 | -98.82 |
| 15 | -6.56 | -74.63 | -68.73 | -164.64 | 11.09 | 60.49 | -4.45 | 147.78 |
| 16 | -8.55 | -110.86 | -50.5 | 34.82 | 25.96 | -9.8 | -7.42 | 28.14 |
| 17 | -21.82 | 158.45 | -47.79 | -154.06 | 30.06 | -97.09 | -21.59 | -124.08 |
| 18 | -20.12 | 105.85 | -47.56 | 64.78 | 29.72 | -80.74 | -25.98 | 145.4 |
| 19 | -18.19 | 32.08 | -48.64 | -69.35 | 29.51 | 121.52 | -12.16 | 63.75 |
| 20 | -16.61 | -4.39 | -52.87 | 170.55 | 29.08 | 20.96 | -8.62 | -21.51 |
| 21 | -20.54 | -26.43 | -52.02 | 50.05 | 30.47 | -53.85 | -8 | -104.67 |
| 22 | -11.9 | -90.46 | -50.73 | -94.94 | 31.37 | -22.03 | -14.3 | 134.42 |
| 23 | -5.91 | -132.86 | -54.95 | 119.41 | 29.52 | -96.73 | -13.07 | -45.69 |
| 24 | -3.93 | -126.93 | -58.6 | -51.47 | 26.82 | -165.81 | -6.18 | -122.92 |
| 25 | -2.54 | -132.34 | -48.6 | 142.44 | 13.28 | 127.59 | -3.25 | 157.78 |
| 26 | -1.86 | 165.98 | -43.17 | 24.67 | -1.9 | 55.27 | -2.46 | 84.78 |
| 27 | -1.5 | 88.14 | -40.28 | -74.67 | -18.4 | -16.22 | -2.05 | 11.35 |
| 28 | -1.21 | 27.28 | -40.41 | 12.21 | -50.97 | -83.24 | -1.63 | -61.16 |
| 29 | -1.06 | -50.26 | -41.18 | -60.44 | -35.1 | -143.59 | -1.22 | -126.47 |
| 30 | -0.83 | -93.99 | -46.02 | -121.63 | -39.72 | 161.99 | -0.87 | 175.17 |
| 31 | -0.71 | -161.49 | -46.75 | 175.52 | -40.74 | 109.41 | -0.77 | 121.4 |
| 32 | -0.7 | 129.48 | -51.73 | 105 | -45.45 | 56.88 | -0.72 | 69.66 |
| 33 | -0.73 | 150.08 | -70.34 | 41.68 | -56 | 1.27 | -0.75 | 16.58 |
| 34 | -0.78 | 137.93 | -63.91 | -102.36 | -61.93 | -58.05 | -0.69 | -38.54 |
| 35 | -0.84 | 33.97 | -71.4 | -178.9 | -58.15 | -117.21 | -0.76 | -94.9 |
| 36 | -0.82 | 174.87 | -49.31 | 167.68 | -50.41 | -172.48 | -0.73 | -150.68 |
| 37 | -0.71 | 137.65 | -42.86 | 134.01 | -43.49 | 137.66 | -0.69 | 156.2 |
| 38 | -0.64 | 58.57 | -40.81 | 54.29 | -40.14 | 91.51 | -0.67 | 106.76 |
| 39 | -0.63 | -4.68 | -37.92 | -5.34 | -37.94 | 45.8 | -0.7 | 57.53 |
| 40 | -0.69 | -56.18 | -37 | -59.52 | -37.04 | -0.63 | -0.83 | 7.25 |

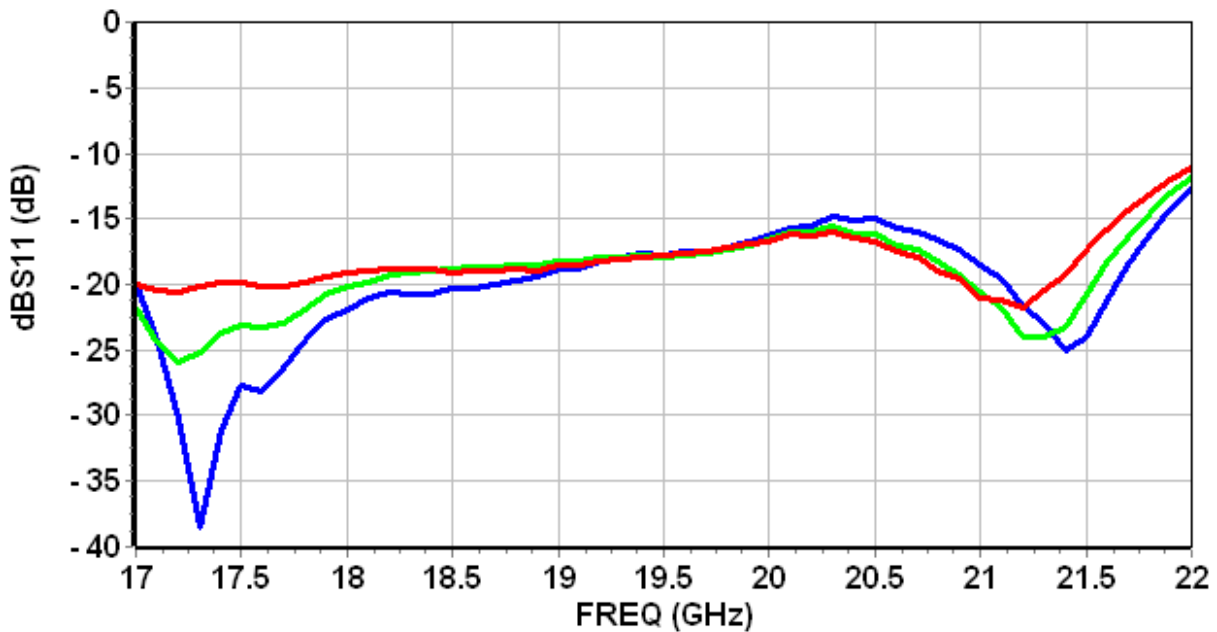
Typical Test Fixture Measurements : Small Signal Performances

$T_{case} = -30^{\circ}C / 25^{\circ}C / 85^{\circ}C$ (Chip Backside), $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case} = 25^{\circ}C$).

Linear Gain versus Frequency & temperature



— $T_{case} = -30^{\circ}C$ — $T_{case} = 25^{\circ}C$ — $T_{case} = 85^{\circ}C$
Input Return Losses versus Frequency & temperature



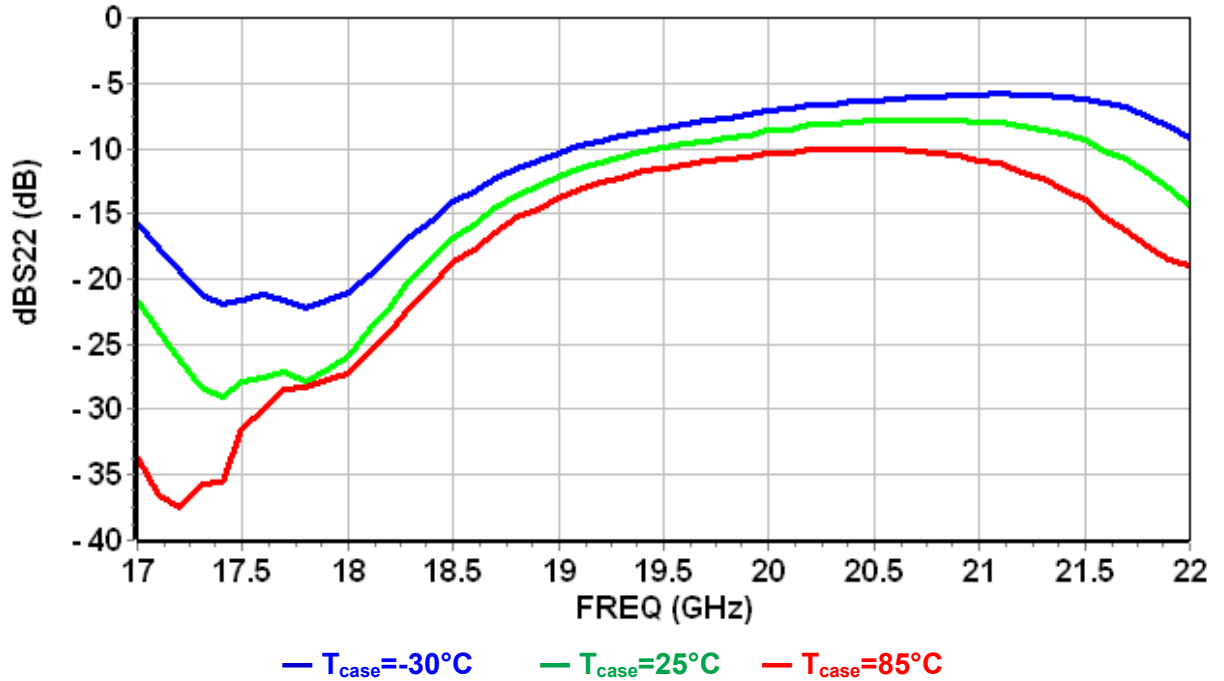
— $T_{case} = -30^{\circ}C$ — $T_{case} = 25^{\circ}C$ — $T_{case} = 85^{\circ}C$



Typical Test Fixture Measurements : Small Signal Performances

$T_{case} = -30^{\circ}C / 25^{\circ}C / 85^{\circ}C$ (Chip Backside), $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case} = 25^{\circ}C$).

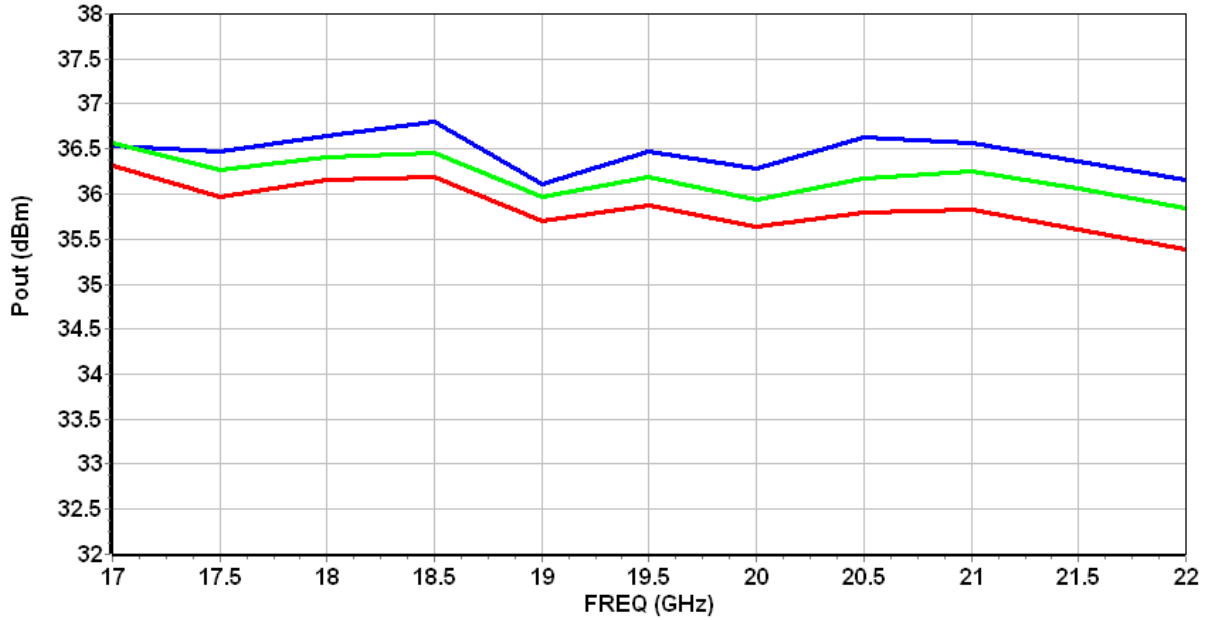
Output Return Losses versus Frequency & temperature



Typical Test Fixture Measurements : Non-linear performances

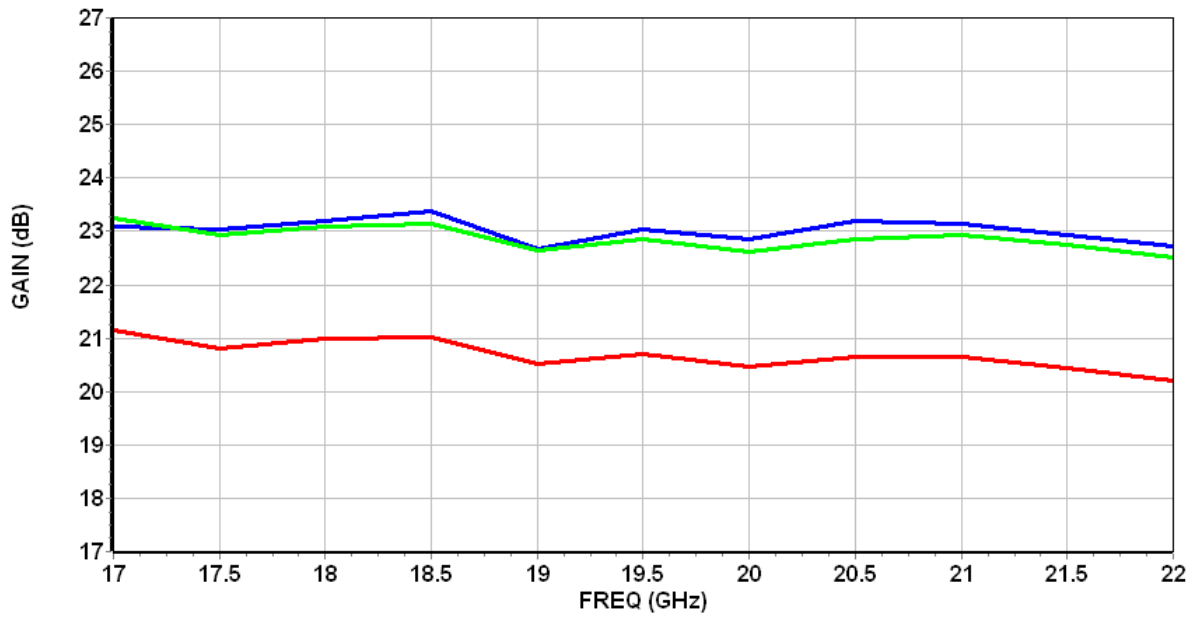
CW measurements: $P_{in}=14\text{dBm}$, $V_d = +18\text{V}$, $I_{dq} = 182\text{mA}$ (Adjusted at $T_{case}=25^\circ\text{C}$).

Output power versus Frequency & temperature



— $T_{case}=-30^\circ\text{C}$ — $T_{case}=25^\circ\text{C}$ — $T_{case}=85^\circ\text{C}$

Gain versus Frequency & temperature



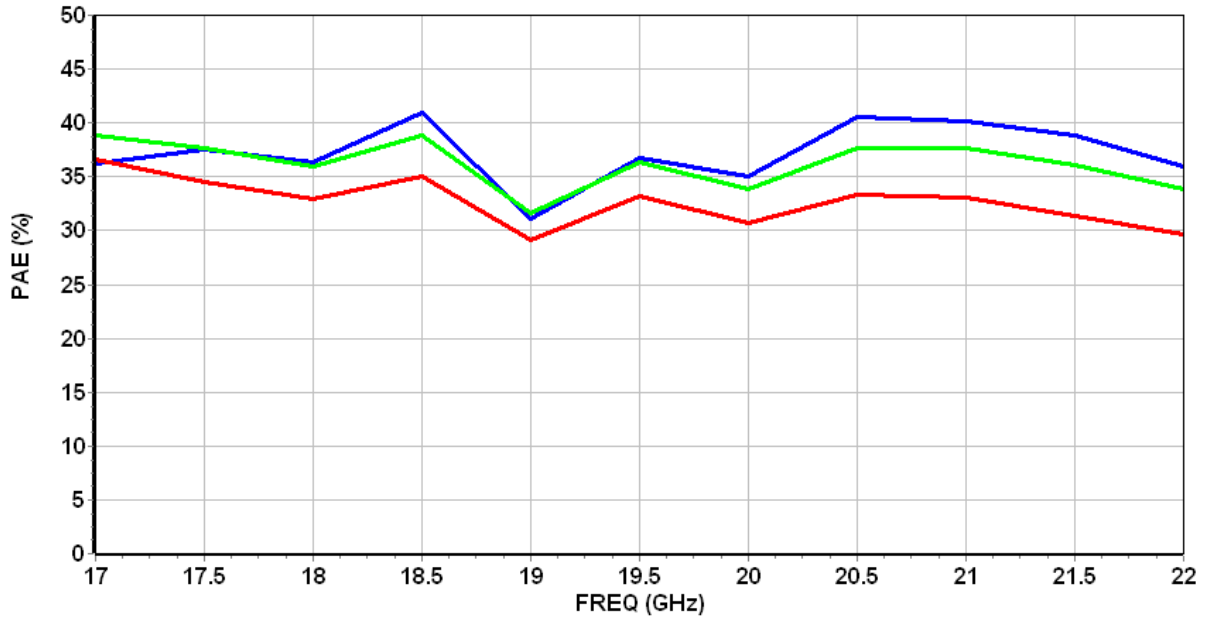
— $T_{case}=-30^\circ\text{C}$ — $T_{case}=25^\circ\text{C}$ — $T_{case}=85^\circ\text{C}$



Typical Test Fixture Measurements : Non-linear performances

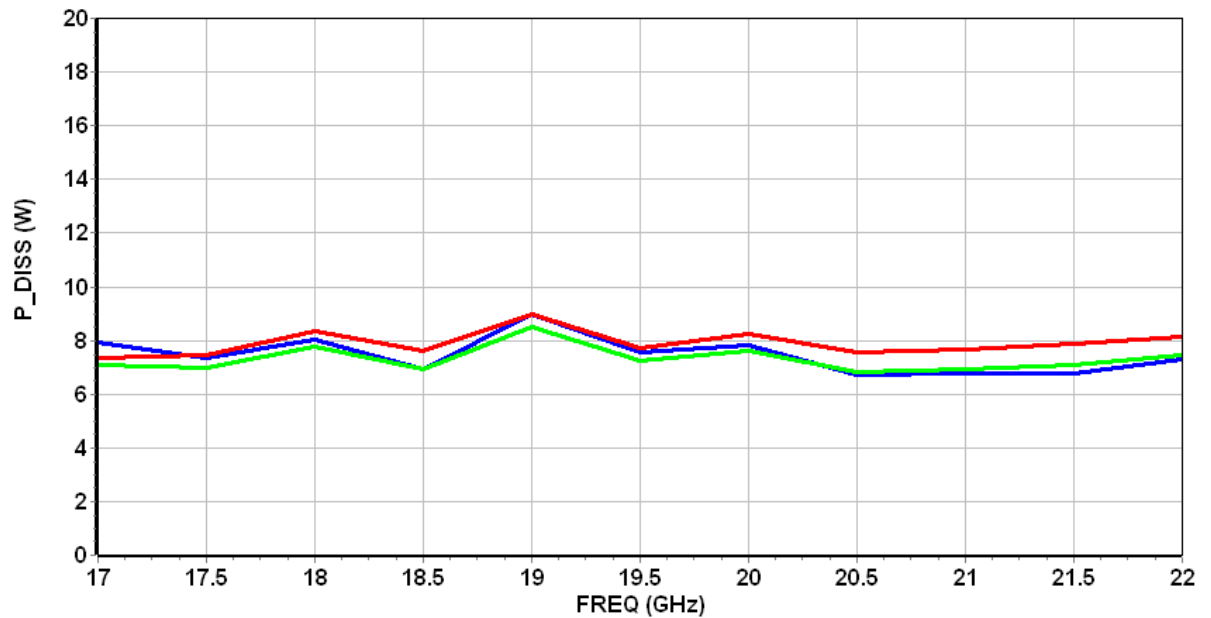
CW measurements: $P_{in}=14\text{dBm}$, $V_d = +18\text{V}$, $I_{dq} = 182\text{mA}$ (Adjusted at $T_{case}=25^\circ\text{C}$).

Power Added Efficiency vs Frequency & temperature



— $T_{case}=-30^\circ\text{C}$ — $T_{case}=25^\circ\text{C}$ — $T_{case}=85^\circ\text{C}$

Dissipated Power versus Frequency & temperature



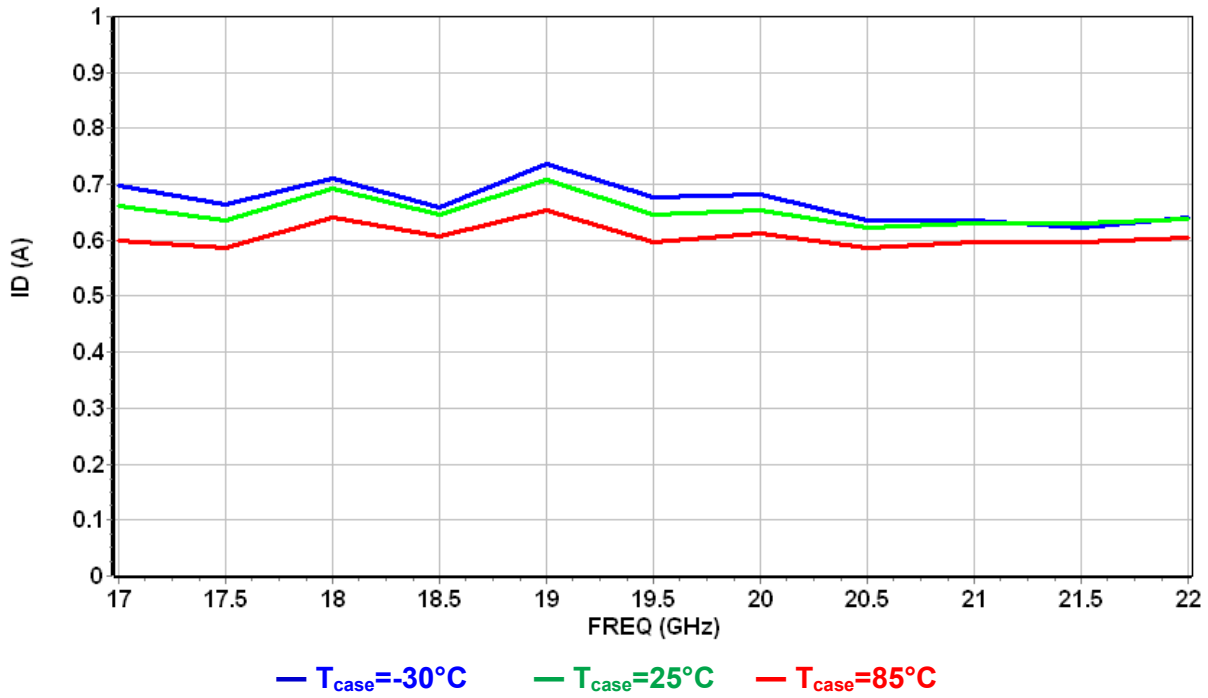
— $T_{case}=-30^\circ\text{C}$ — $T_{case}=25^\circ\text{C}$ — $T_{case}=85^\circ\text{C}$



Typical Test Fixture Measurements : Non-linear performances

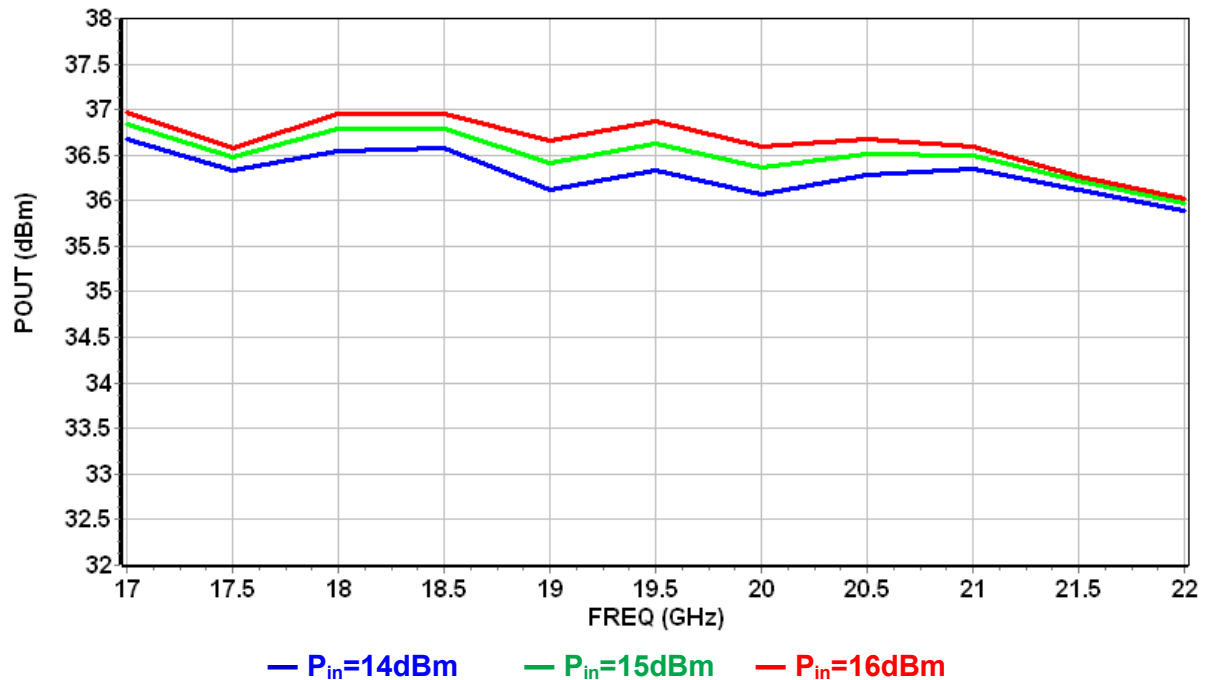
CW measurements: $P_{in}=14\text{dBm}$, $V_d = +18\text{V}$, $I_{dq} = 182\text{mA}$ (Adjusted at $T_{case}=25^\circ\text{C}$).

Drain current vs Frequency & temperature



Output power versus Frequency & Input Power

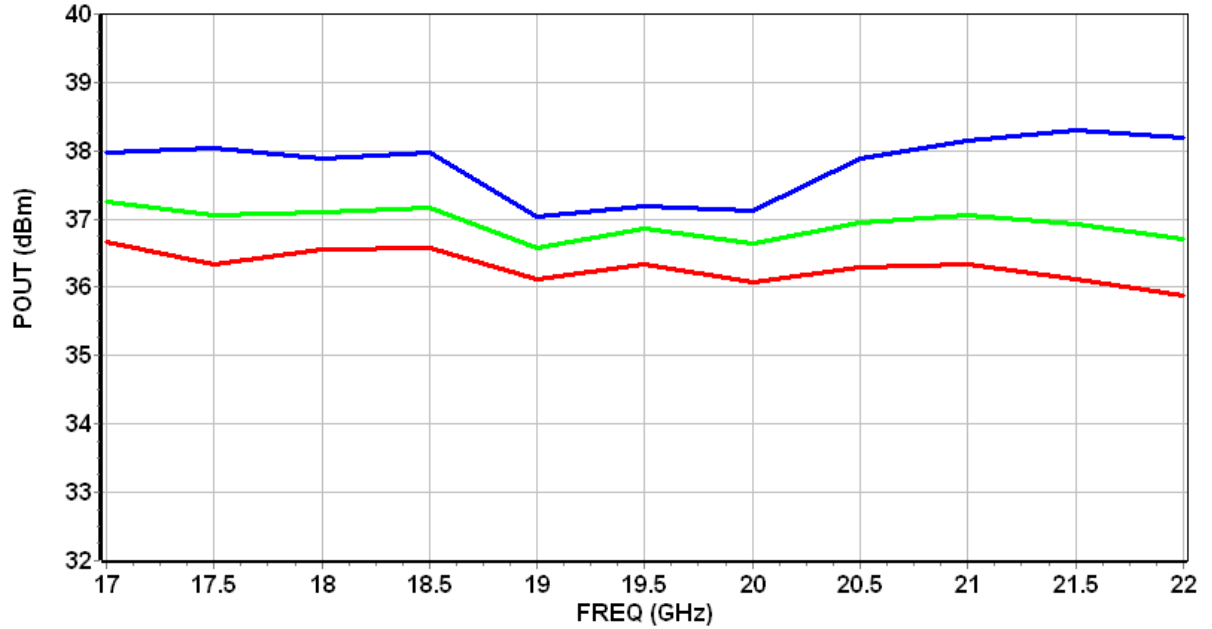
CW measurements: $T_{case}=+25^\circ\text{C}$, $V_d = +18\text{V}$, $I_{dq} = 182\text{mA}$ (Adjusted at $T_{case}=25^\circ\text{C}$).



Typical Test Fixture Measurements : Non-linear performances

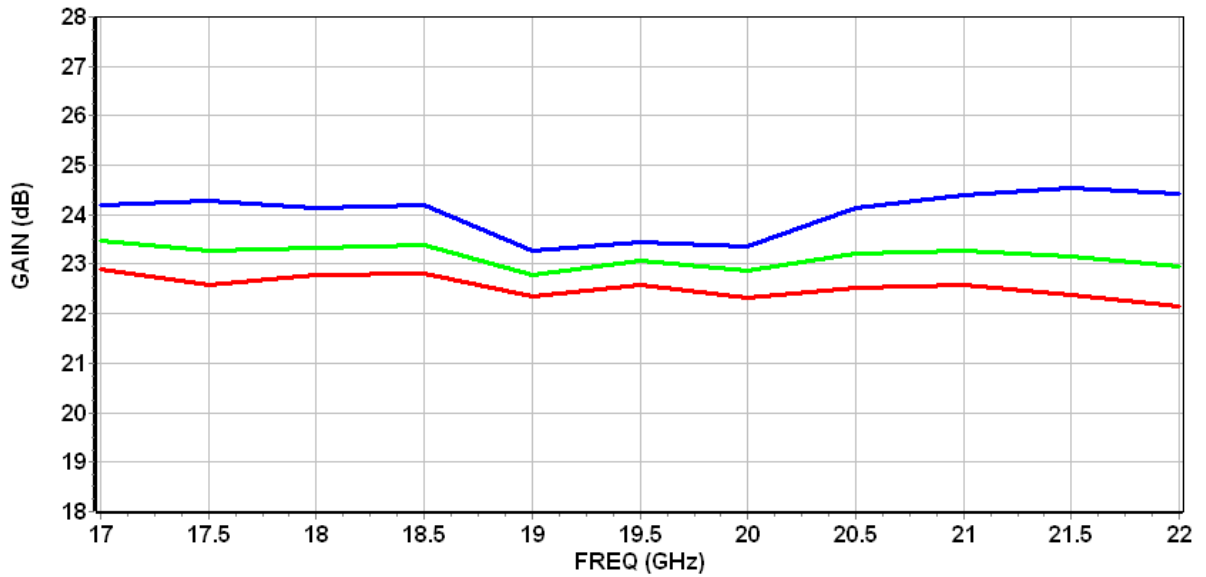
CW measurements: $T_{case}=+25^{\circ}C$, $P_{in}=14dBm$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Output Power vs Frequency & Drain Voltage



— Vd=25V — Vd=20 — Vd=18V

Gain versus Frequency & Drain Voltage



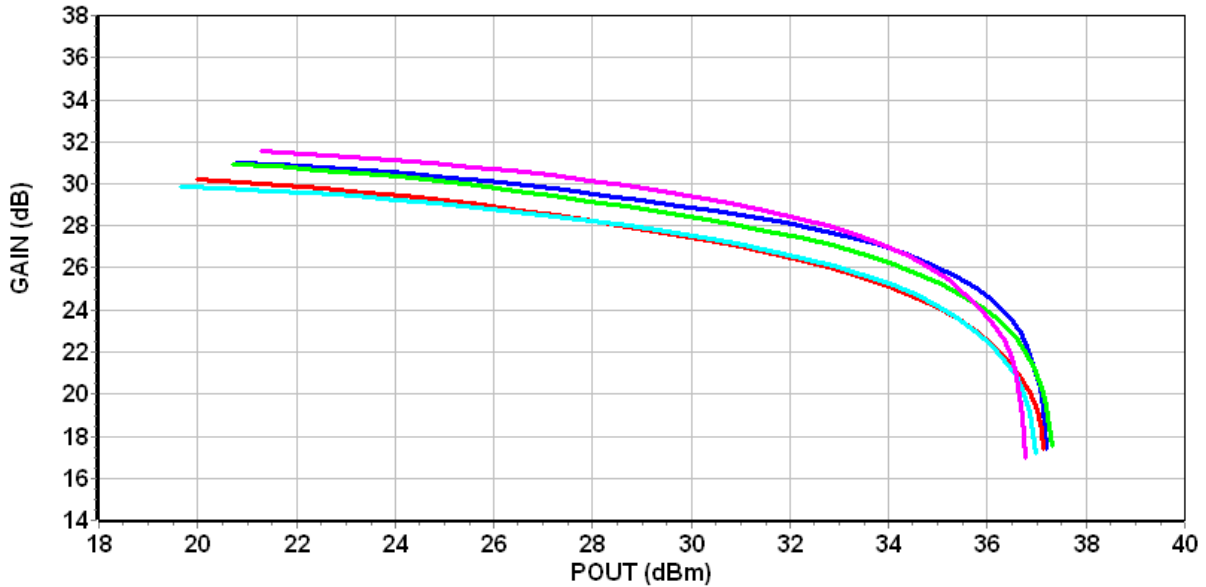
— Vd=25V — Vd=20 — Vd=18V



Typical Test Fixture Measurements : Non-linear performances

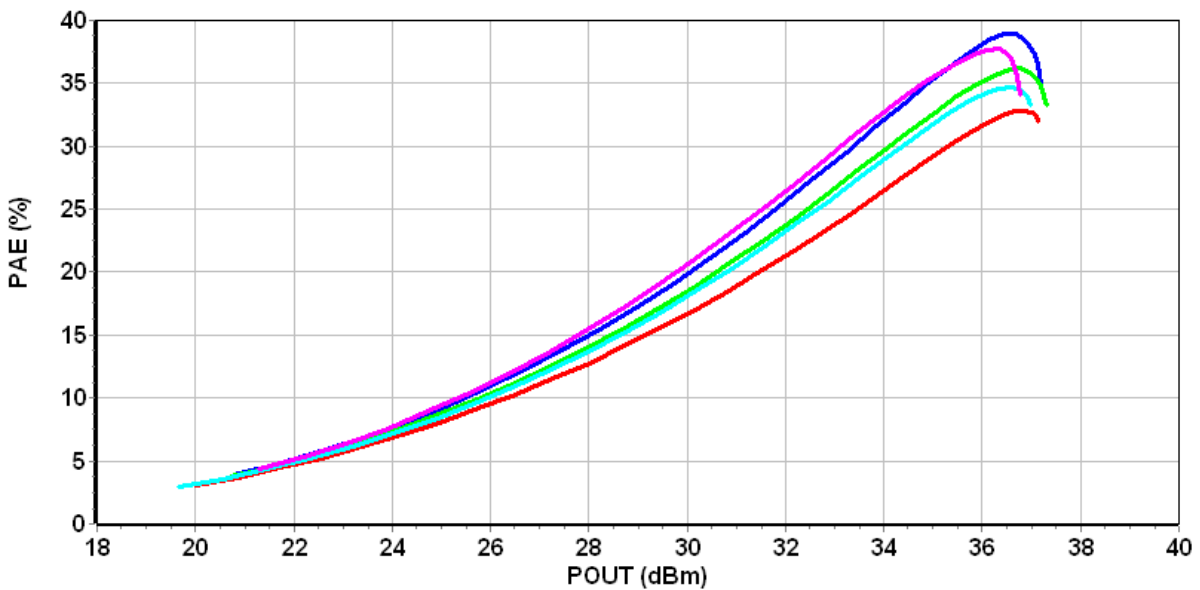
CW measurements: $T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Gain versus Output Power & Frequency



— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz

Power Added Efficiency versus Output Power & Frequency



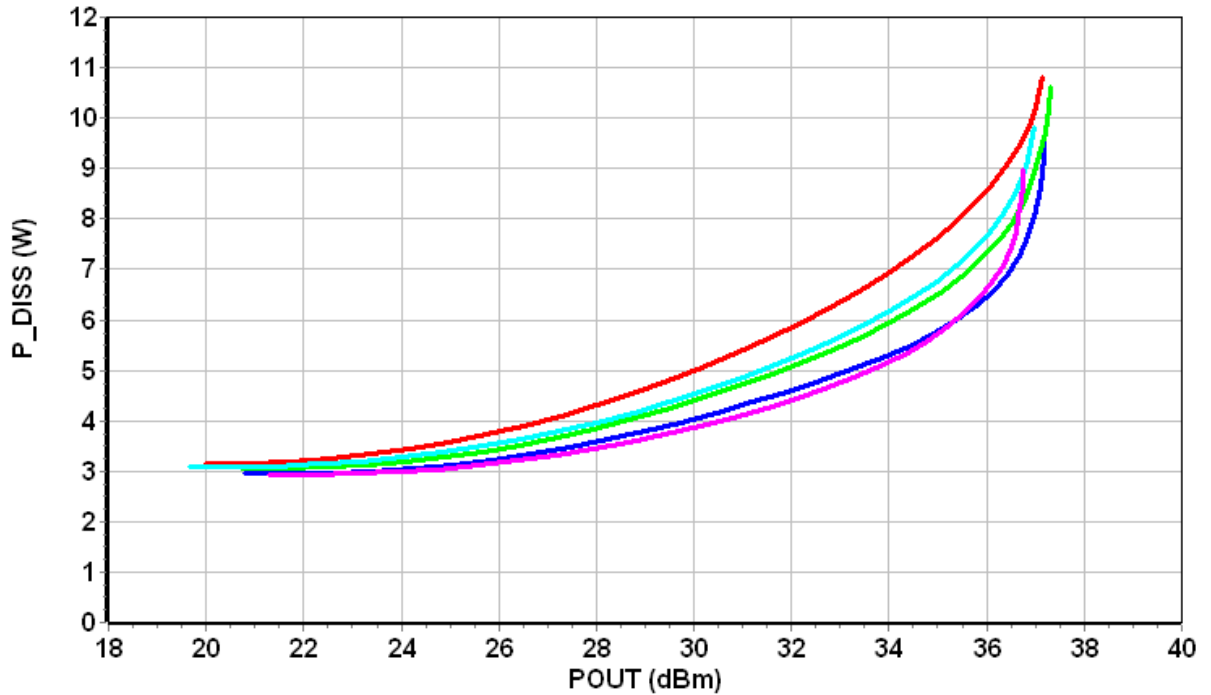
— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz



Typical Test Fixture Measurements : Non-linear performances

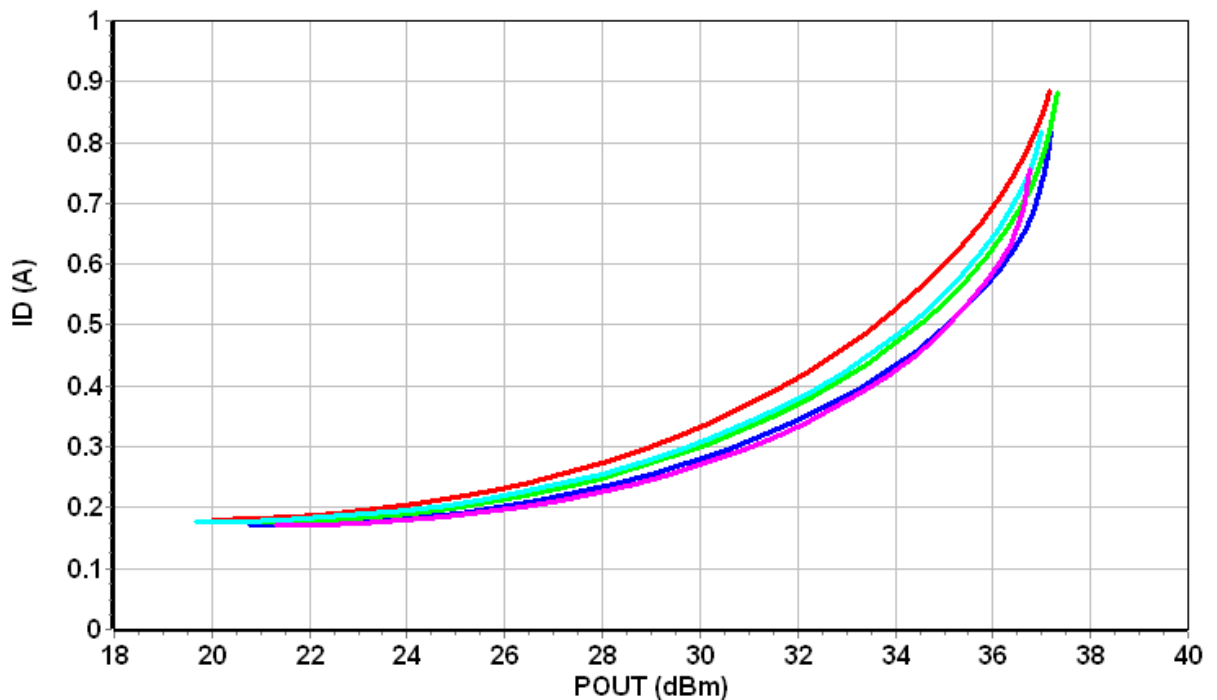
CW measurements: $T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Dissipated Power versus Output Power & Frequency



— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz

Drain Current versus Output Power & Frequency



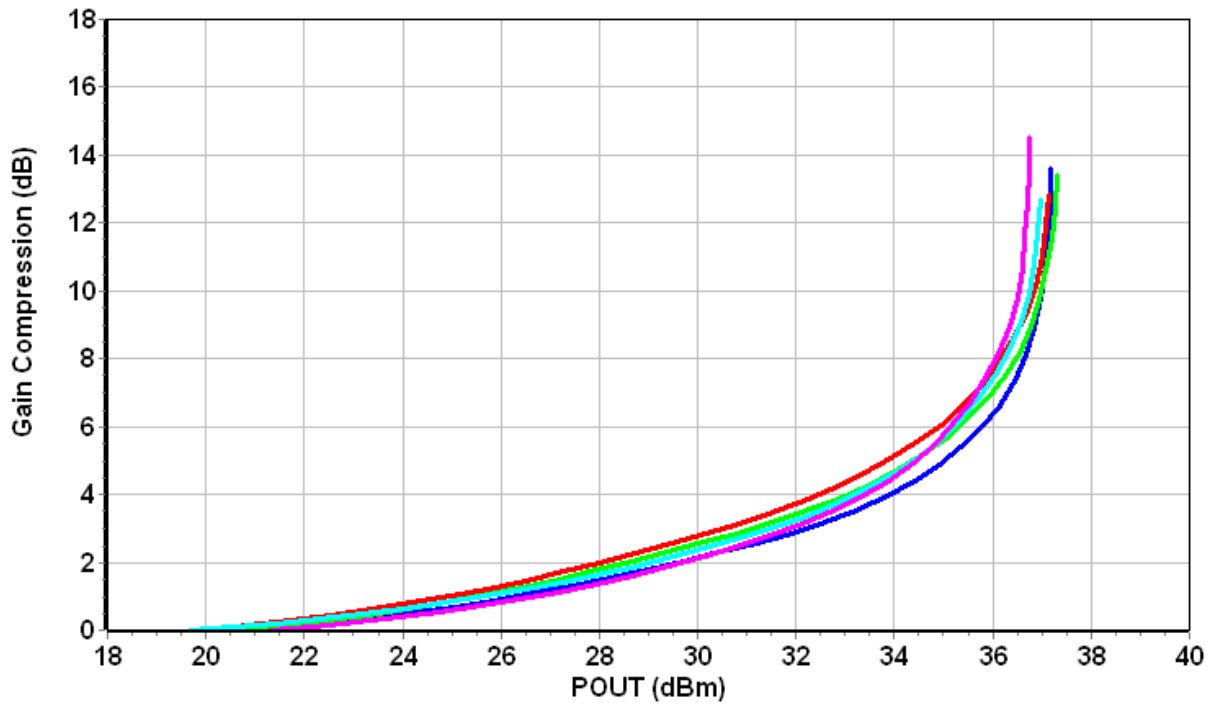
— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz



Typical Test Fixture Measurements : Non-linear performances

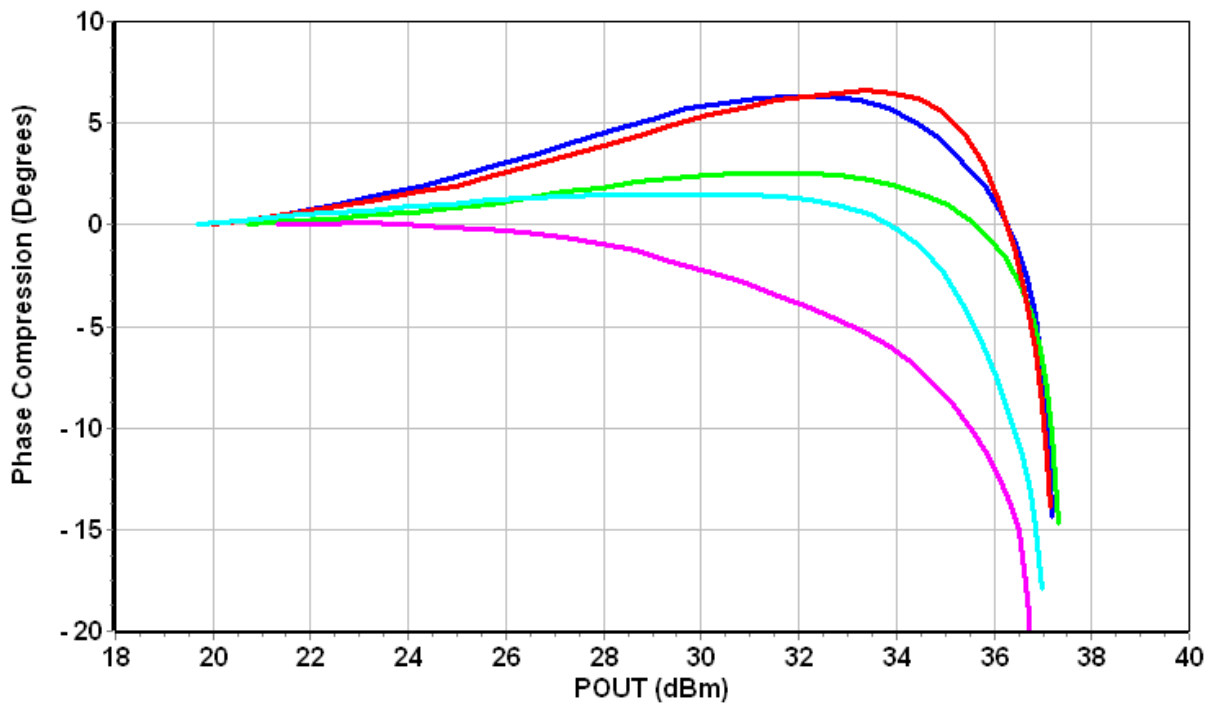
CW measurements: $T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Gain Compression versus Output Power & Frequency



— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz

Phase Compression versus Output Power & Frequency



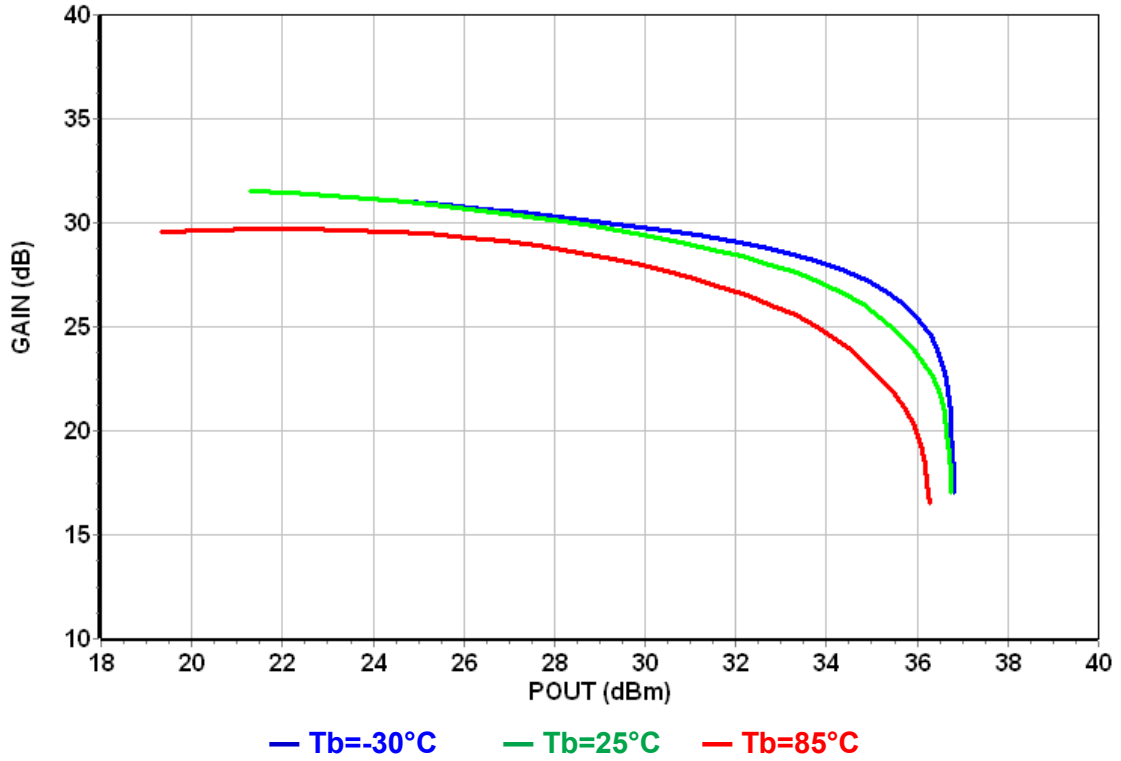
— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz



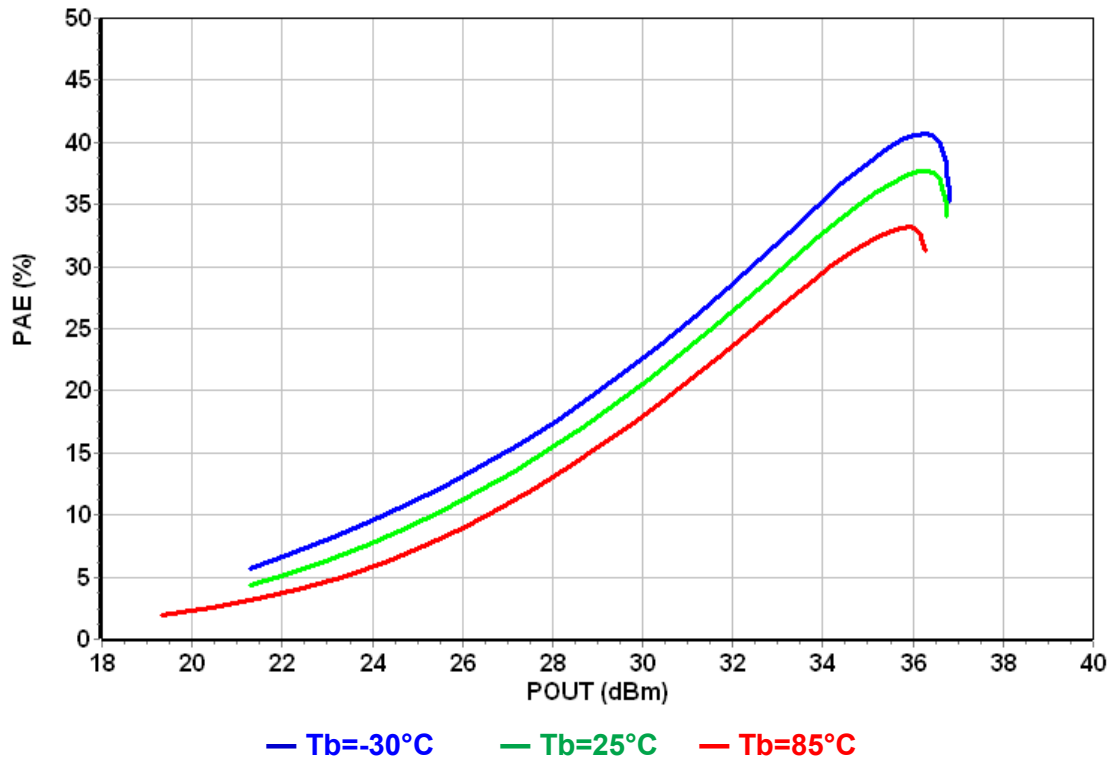
Typical Test Fixture Measurements : Non-linear performances

CW measurements: $V_d = +18V$, $I_{dq} = 182mA$, Frequency=21GHz (Adjusted at $T_{case}=25^{\circ}C$).

Gain versus Output Power & Temperature



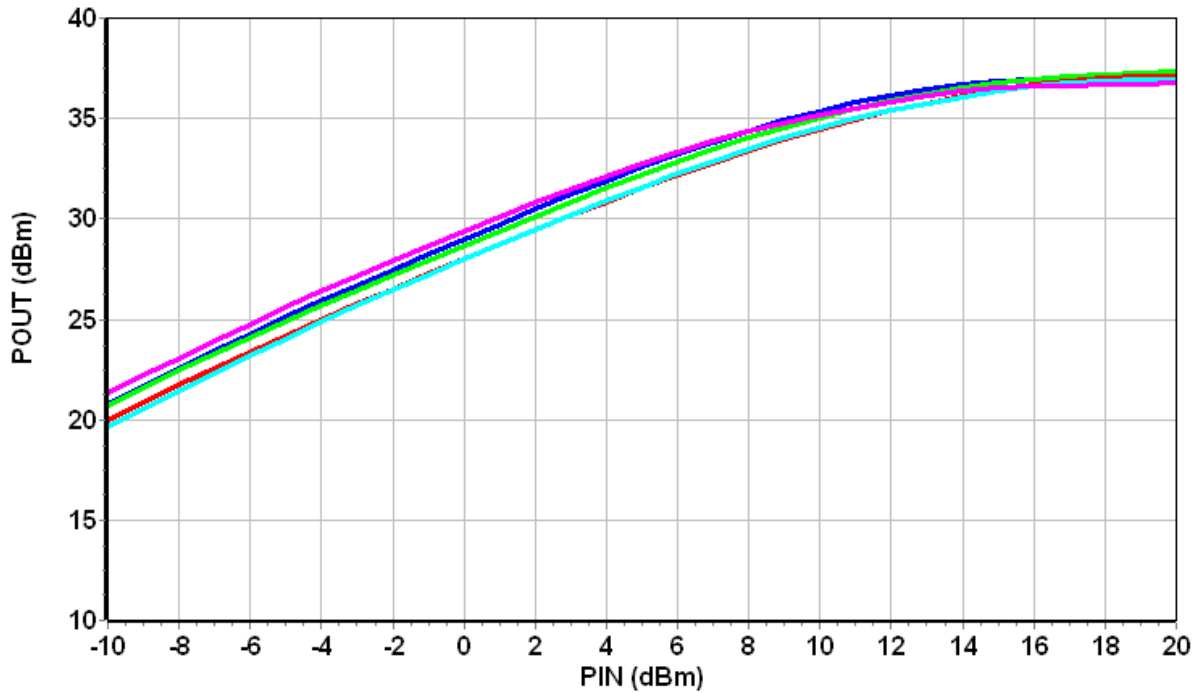
Power Added Efficiency versus Output Power & Temperature



Typical Test Fixture Measurements : Non-linear performances

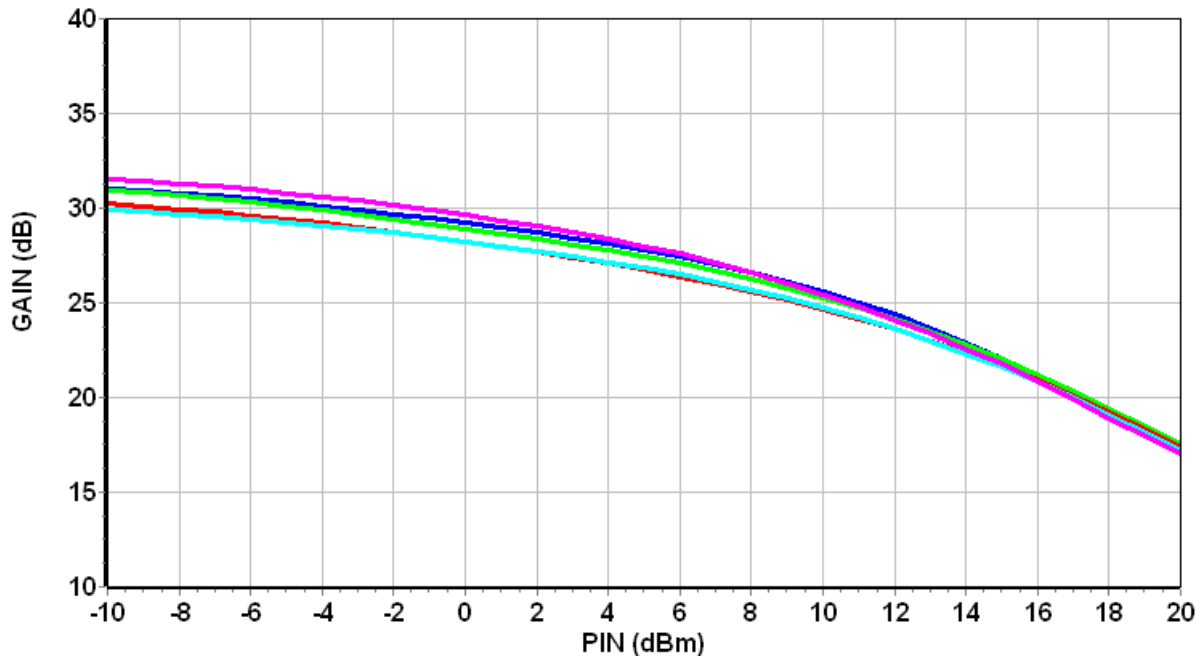
CW measurements: $T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Output Power versus Input Power & Frequency



— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz

Gain versus Input Power & Frequency



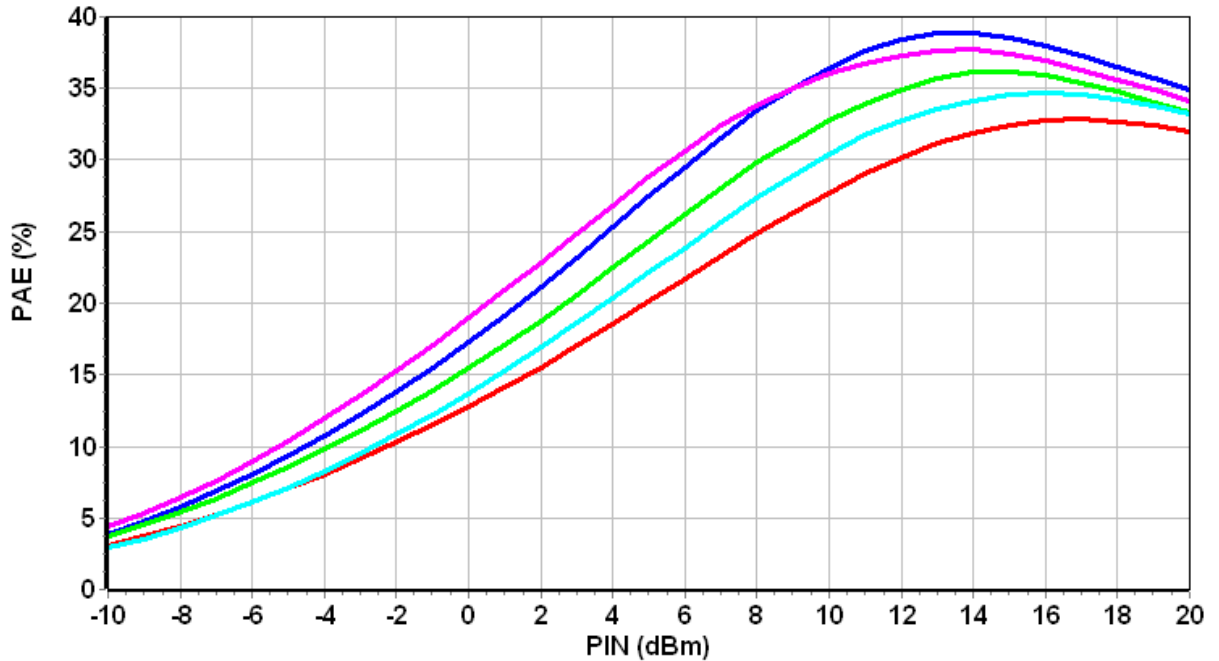
— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz



Typical Test Fixture Measurements : Non-linear performances

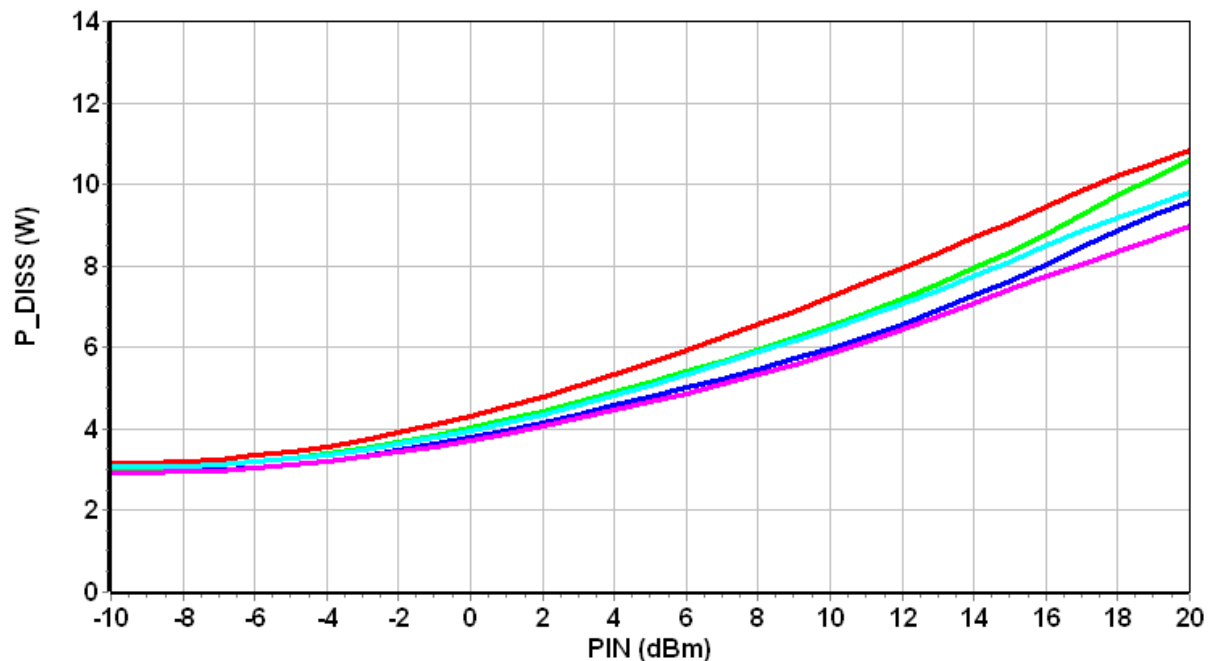
CW measurements: $T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Power Added Efficiency versus Input Power & Frequency



— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz

Dissipated Power versus Input Power & Frequency



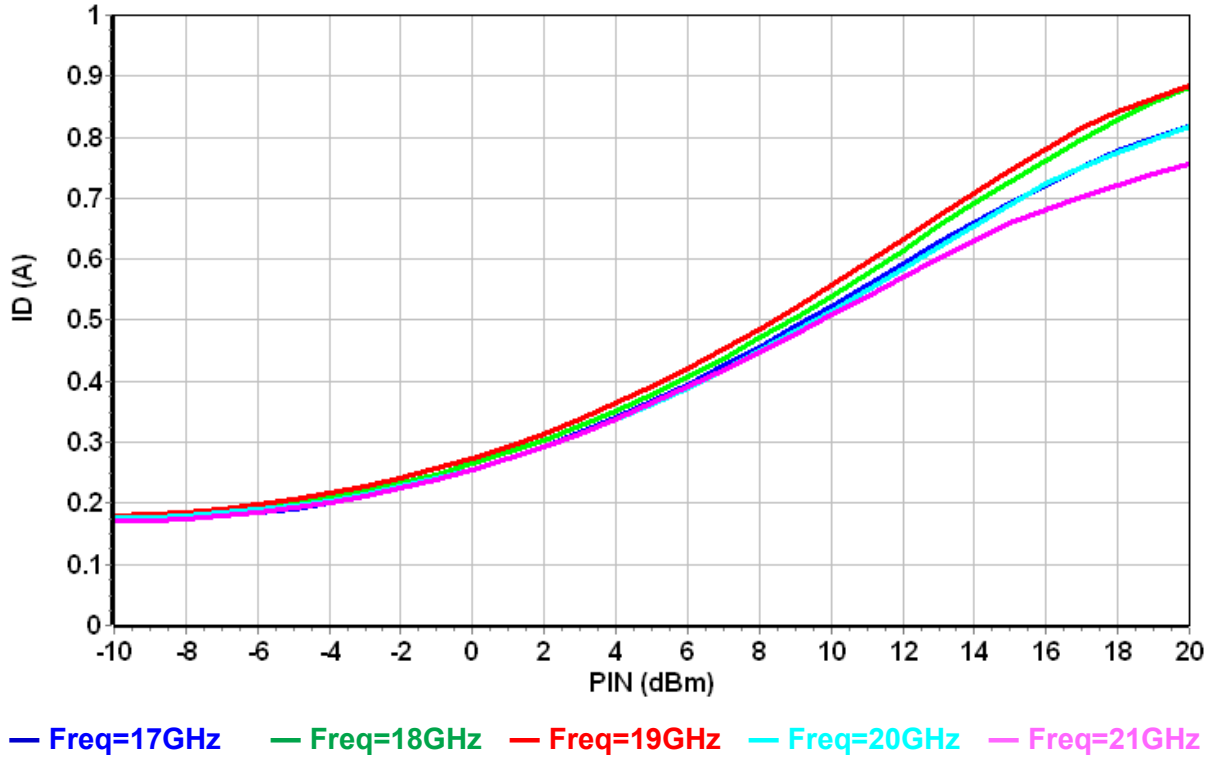
— Freq=17GHz — Freq=18GHz — Freq=19GHz — Freq=20GHz — Freq=21GHz



Typical Test Fixture Measurements : Non-linear performances

CW measurements: $T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$ (Adjusted at $T_{case}=25^{\circ}C$).

Drain Current versus Input Power & Frequency



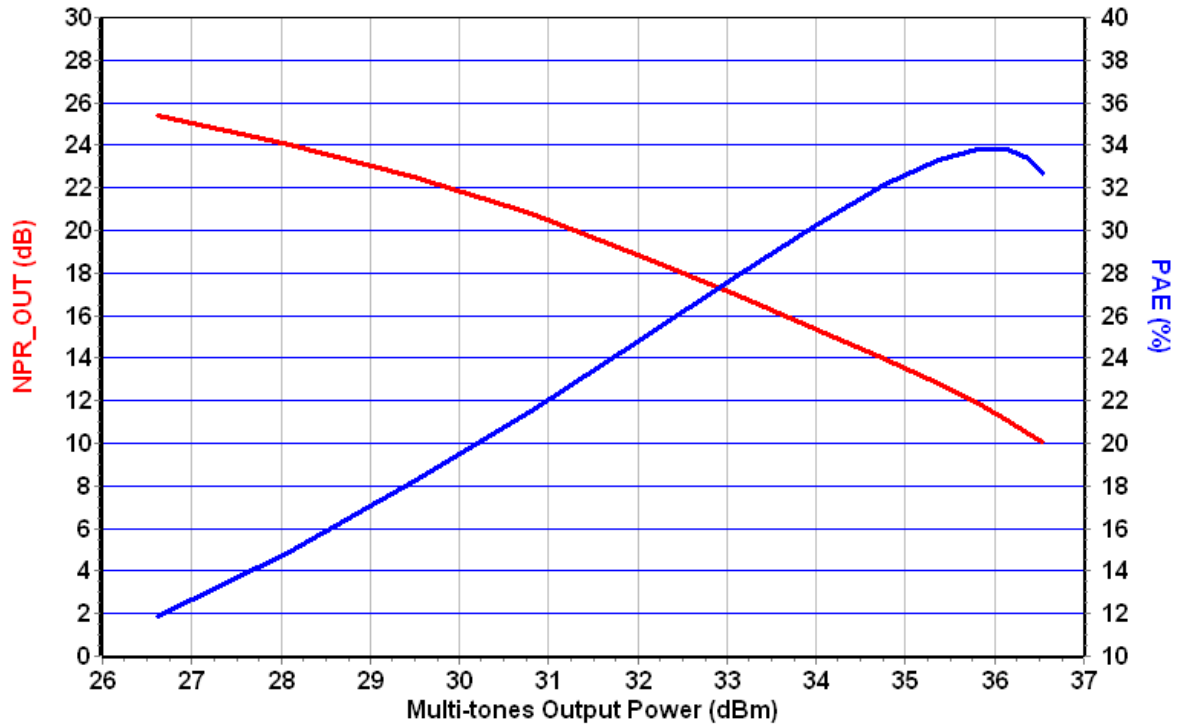
Typical Test Fixture Measurements : NPR performances

$T_{case}=+25^{\circ}C$, $V_d = +18V$, $I_{dq} = 182mA$

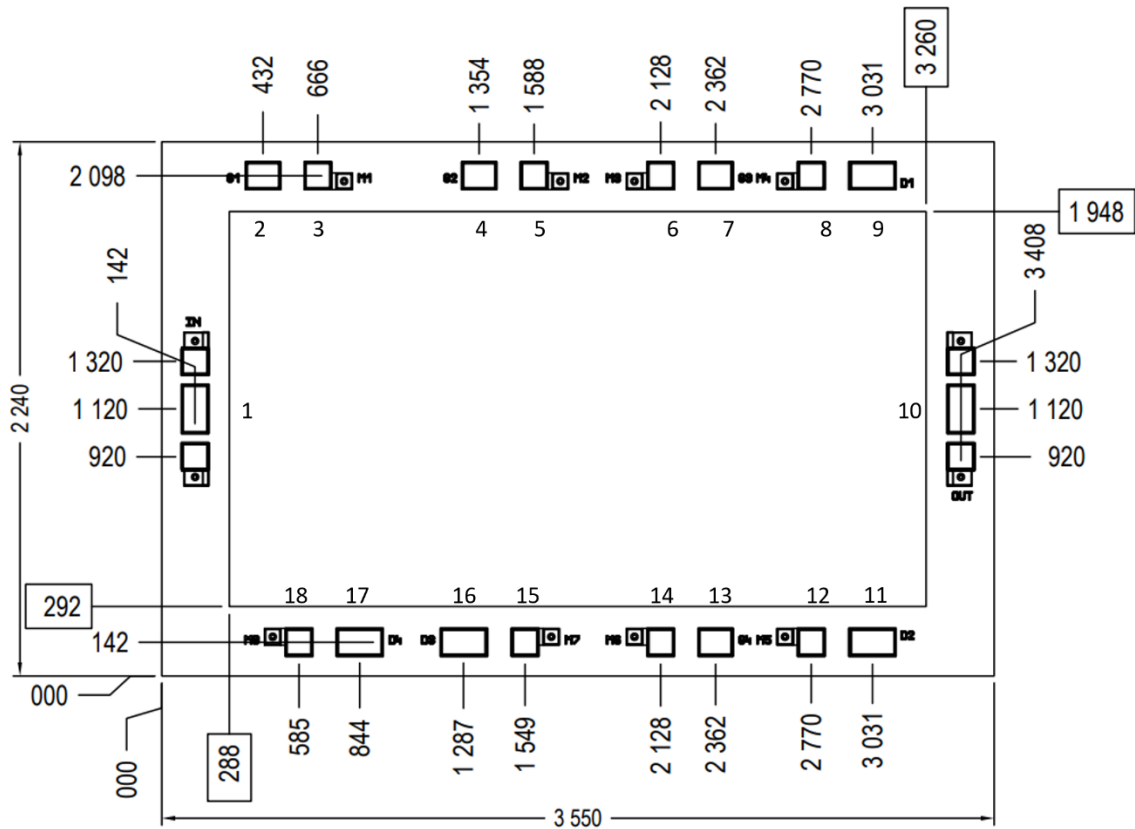
Center Frequency : 19.3GHz

Measured bandwidth : 45MHz

Notch width : 2MHz



Chip Mechanical data



All dimensions are in micrometres.

Chip size = 3550x2240 ±50µm

Chip thickness = 70µm ±10µm

Chip width and length are given with a tolerance of ±50µm

RF pads (1, 10) = 208 x 118µm²

DC pads (3, 5, 6, 8, 12, 14, 15, 18) = 118 x 118µm²

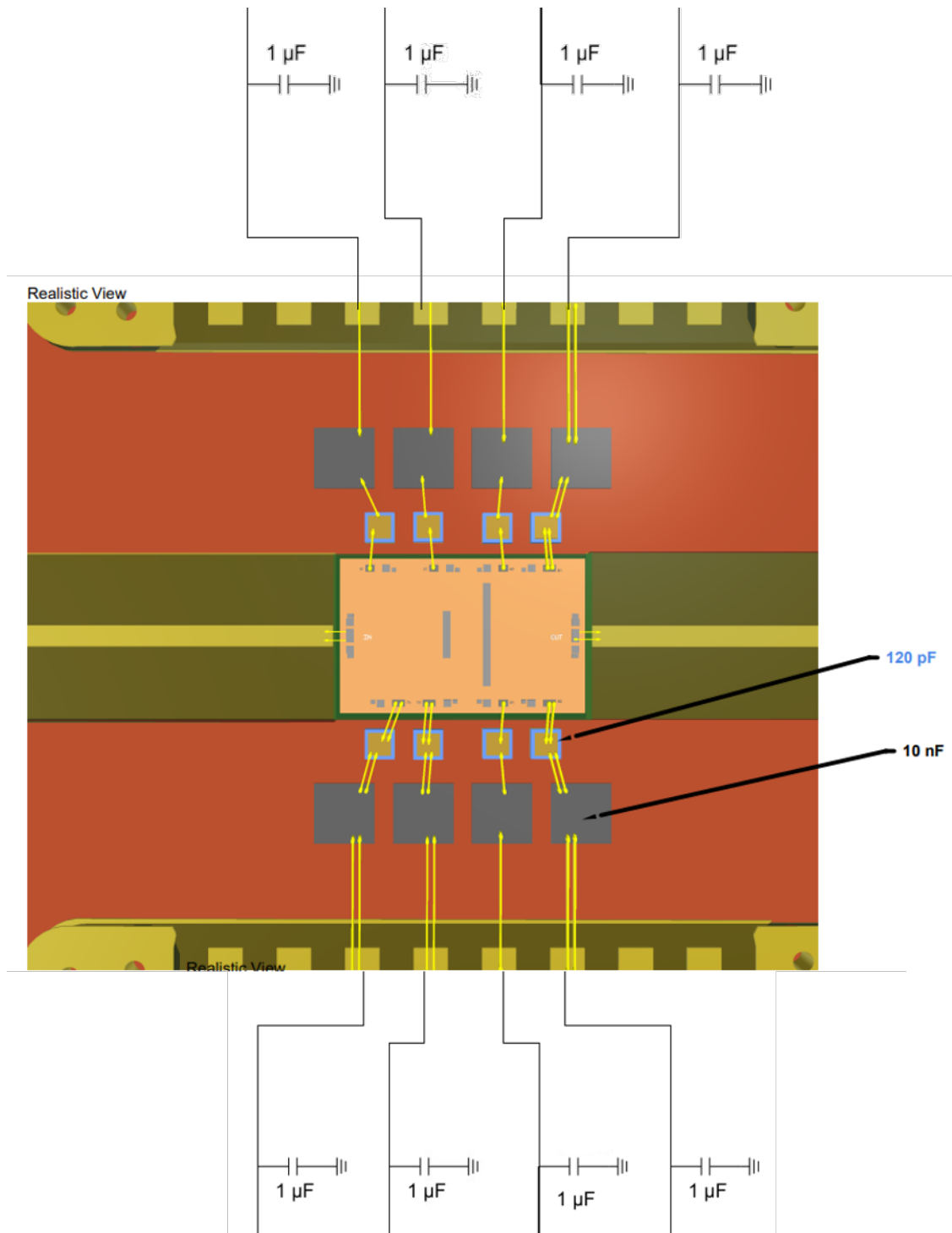
DC pads (2, 4, 7, 13) = 150 x 118µm²

DC pads (9, 11, 16) = 203 x 118µm²

DC pads (17) = 200 x 118µm²

| PAD Number | Name | Description |
|----------------------------|------|----------------------------------------|
| 1 | IN | RF input |
| 3, 5, 6, 8, 12, 14, 15, 18 | GND | Ground (Not connected) |
| 2 | VG1 | Gate voltage of 1 st stage |
| 4 | VG2 | Gate voltage of 2 nd stage |
| 7, 13 | VG3 | Gate voltage of 3 rd stage |
| 17 | VD1 | Drain voltage of 1 st stage |
| 16 | VD2 | Drain voltage of 2 nd stage |
| 9, 11 | VD3 | Drain voltage of 3 rd stage |
| 10 | OUT | RF output |

Recommended assembly plan

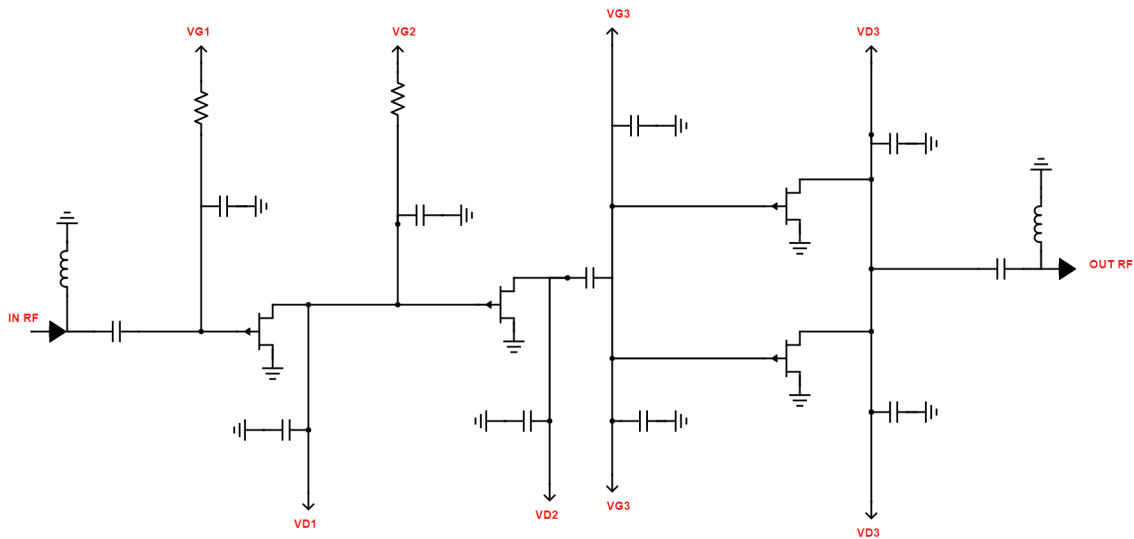


3 levels of decoupling capacitor have been used:

- First level of capacitor is 120pF
- Second level is 10nF
- Third level is 1μF on SMB connectors

DC Schematic

Due to ESD protection circuits on RF input and output, an external capacitance might be requested to isolate the product from external voltage that could be present on the RF accesses.



The DC connections do not include any decoupling capacitor in package, therefore it is mandatory to provide a good external DC decoupling (120pF, 10nF, 1 μ F) on the PC board, as close as possible to the die.

Notes:



Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com>.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com> for ESD sensitivity and handling recommendations for the UMS package products.

Ordering Information

CHA6262-99F/XY

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